## SPICE Device Model SiJA52ADP



Vishay Siliconix

# N-Channel 40 V (D-S) MOSFET

#### DESCRIPTION

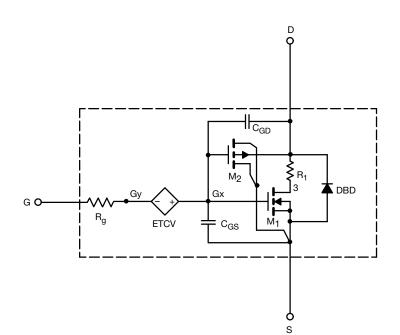
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over -55 °C to +125 °C temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

### **CHARACTERISTICS**

- N-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over -55 °C to +125 °C temperature range
- Model the gate charge

### SUBCIRCUIT MODEL SCHEMATIC



#### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits



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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static	•				
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	1.8	-	V
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	0.0013	0.0013	Ω
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	0.0020	0.0019	
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 15 \text{ A}$	150	98	S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> = 5 A	0.70	0.71	V
Dynamic <sup>b</sup>					
Input capacitance	C <sub>iss</sub>	$V_{DS}$ = 20 V, $V_{GS}$ = 0 V, f = 1 MHz	5410	5500	pF
Output capacitance	C <sub>oss</sub>		1340	1086	
Reverse transfer capacitance	C <sub>rss</sub>		113	67	
Total gate charge	0	$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 10 \text{ A}$	66	66	nC
	Qg	$V_{DS}$ = 20 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 10 A	31	32	
Gate-source charge	Q <sub>gs</sub>		15	15	
Gate-drain charge	Q <sub>gd</sub>		6	4.5	

Notes

a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing



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-55 °C

= 25 °C

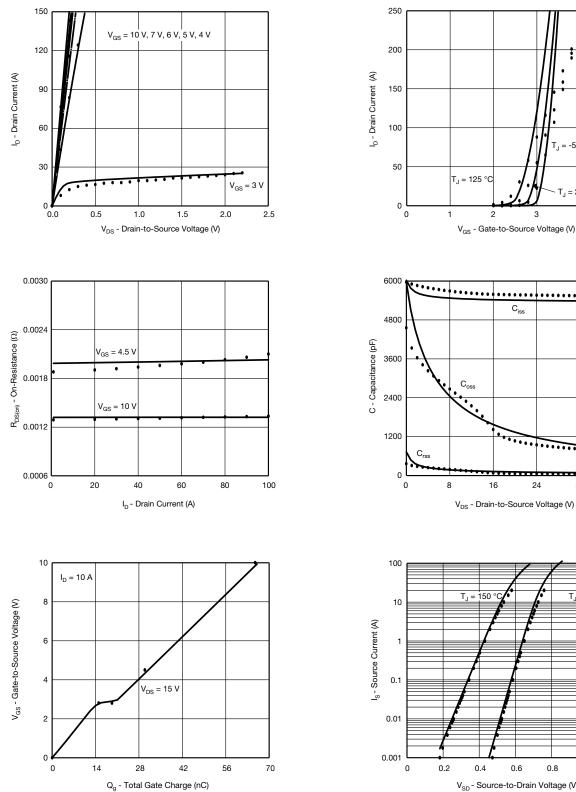
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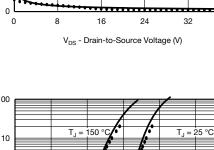
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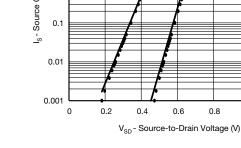
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40

### COMPARISON OF MODEL WITH MEASURED DATA (T<sub>J</sub> = 25 °C, unless otherwise noted)







#### Note

· Dots and squares represent measured data Copyright: Vishay Intertechnology, Inc.

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